



T4SNAL100



1200V SiC MOSFETs

General Description

The 1200V SiC MOSFETs has been especially tailored to minimize on-state resistance, provide superior switching performance, higher system efficiency, and faster operating frequency.

These devices are well suited for high efficiency fast switching applications.

BV_{DSS}	$R_{DS(ON)}$	I_D
1200 V	100 mΩ	35 A

Features

- $R_{DS(ON)} \leq 100m\Omega @ V_{GS}=10V$
- Improved dv/dt Capability
- High Speed Switching
- Green Device Available

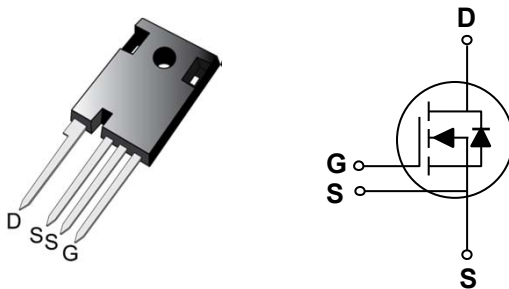
Benefits

- Lower Capacitance
- Higher System Efficiency
- Easy to Parallel

Applications

- Solar Inverters
- Switch Mode Power Supplies, UPS
- Induction Heating and Welding
- EV Charging Stations
- High Voltage DC/DC Converters
- Motor Drives

TO-247-4L Pin Configuration



Maximum Ratings $T_J=25^\circ C$ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	1200	V
$V_{GS(max)}$	Gate-Source Voltage	-10 / +25	V
$V_{GS(op)}$	Gate-Source Voltage (Recommended operational)	-5 / +20	V
I_D	Drain Current – Continuous ($T_C=25^\circ C$, $T_J=175^\circ C$)	35	A
I_D	Drain Current – Continuous ($T_C=100^\circ C$, $T_J=175^\circ C$)	26	A
I_{DM}	Drain Current – Pulsed ($T_C=25^\circ C$) (NOTE 1)	80	A
EAS	Single Pulse Avalanche Energy (NOTE 2)	200	mJ
P_D	Power Dissipation ($T_C=25^\circ C$)	188	W
T_J	Operating Junction Temperature Range	-55 to 175	$^\circ C$
T_{STG}	Storage Temperature Range	-55 to 175	$^\circ C$
Marking Code		SNAL100	

Thermal Characteristics

Symbol	Parameter	Rating	Unit
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	40	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction to Case	0.8	$^\circ C/W$



Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=1mA$	1200	---	---	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=1200V, V_{GS}=0V$	---	---	1	uA
		$V_{DS}=1200V, V_{GS}=0V, T_J=175^\circ\text{C}$	---	1	---	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=20V, V_{DS}=0V$	---	---	100	nA
		$V_{GS}=-5V, V_{DS}=0V$	---	---	-100	

On Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=20V, I_D=20A$	---	---	100	mΩ
		$V_{GS}=20V, I_D=10A$	---	---	90	
		$V_{GS}=20V, I_D=20A, T_J=125^\circ\text{C}$	---	106	---	
		$V_{GS}=20V, I_D=20A, T_J=175^\circ\text{C}$	---	134	---	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=10mA$	2.0	---	4.0	V
		$V_{GS}=V_{DS}, I_D=10mA, T_J=125^\circ\text{C}$	---	2.1	---	
		$V_{GS}=V_{DS}, I_D=10mA, T_J=175^\circ\text{C}$	---	1.9	---	

Dynamic and switching Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Q_g	Total Gate Charge	$V_{DD}=800V, V_{GS}=-5/+20V, I_D=20A$	---	61	---	nC
Q_{gs}	Gate-Source Charge		---	24	---	
Q_{gd}	Gate-Drain Charge		---	14	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=800V, R_G=2.5\Omega, I_D=20A, V_{GS}=-5/+20V$	---	9	---	nS
T_r	Rise Time		---	4	---	
$T_{d(off)}$	Turn-Off Delay Time		---	15	---	
T_f	Fall Time		---	10	---	
C_{iss}	Input Capacitance	$V_{DS}=1000V, V_{GS}=0V, F=200kHz$	---	1377	---	pF
C_{oss}	Output Capacitance		---	62	---	
C_{riss}	Reverse Transfer Capacitance		---	4	---	
E_{oss}	Coss Stored Energy		---	38	---	
$E_{(on)}$	Turn-On Switching Energy	$V_{DD}=800V, R_G=2.5\Omega, I_D=20A, V_{GS}=-5/+20V$	---	208	---	uJ
$E_{(off)}$	Turn-Off Switching Energy		---	25	---	
$E_{(tot)}$	Total Switching Energy		---	233	---	
R_g	Gate Resistance		$V_{GS}=0V, V_{DS}=0V, F=1MHz$	---	3	



Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Drain-Source Diode Characteristics and Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Body Diode Current	$V_{GS} = -5V, T_C = 25^\circ\text{C}$	---	---	43	A
V_{SD}	Diode Forward Voltage	$V_{GS} = -5V, I_S = 10A$	---	3.8	---	V
t_{rr}	Reverse Recovery Time	$V_{GS} = -5V, I_S = 20A, V_R = 800V, di_F/dt = 8.0A/ns$	---	8	---	nS
Q_{rr}	Reverse Recovery Charge		---	130	---	nC
I_{RRM}	Peak Reverse Recovery Current		---	29	---	A

NOTES :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. $I_{AS}=20A, V=50V, L=1mH$.

Typical Performance

FIG. 1-Output Characteristics $T_J=25^\circ\text{C}$

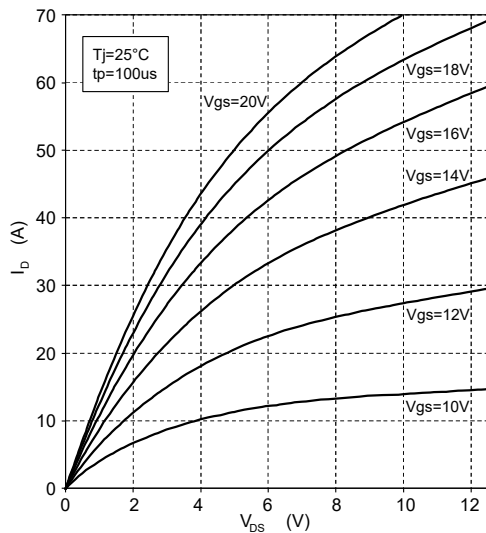
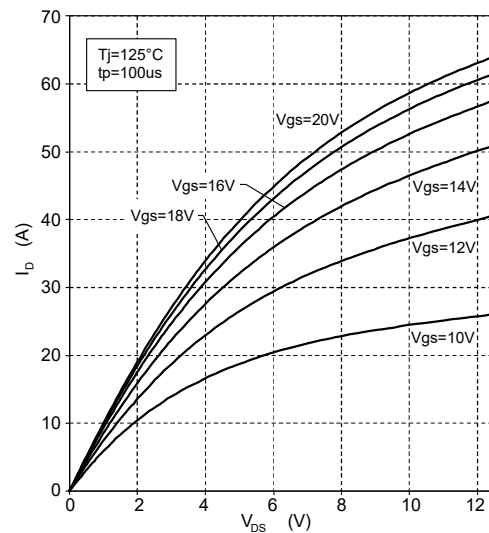


FIG. 2-Output Characteristics $T_J=125^\circ\text{C}$





Typical Performance

FIG. 3-Output Characteristics $T_J=175^{\circ}\text{C}$

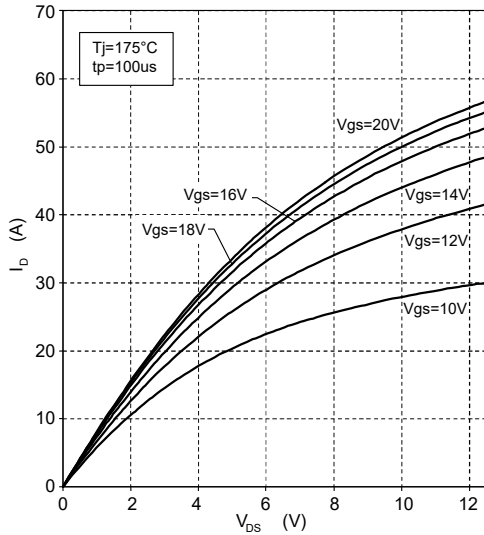


FIG. 4-Normalized $R_{DS(ON)}$ vs T_J

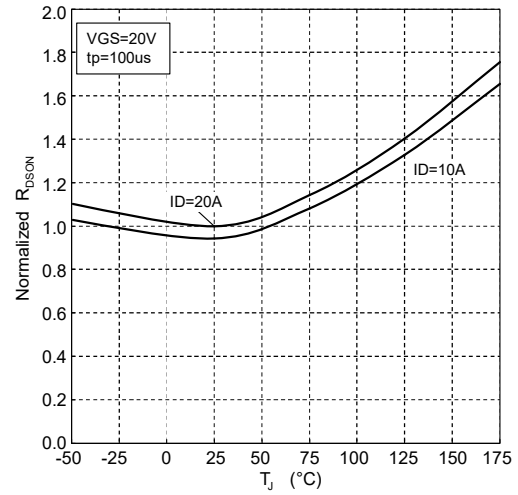


FIG. 5-Transfer Characteristic

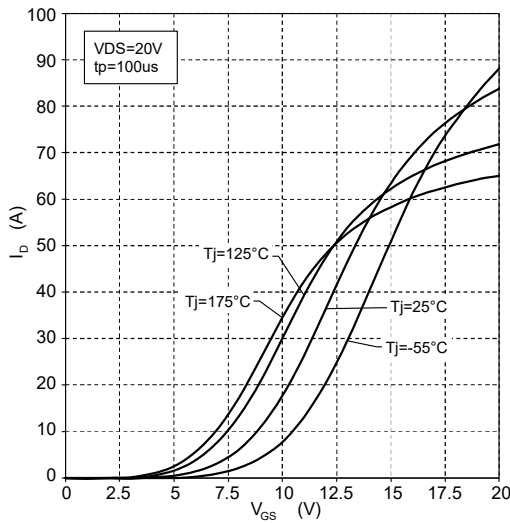


FIG. 6-Body Diode Characteristics

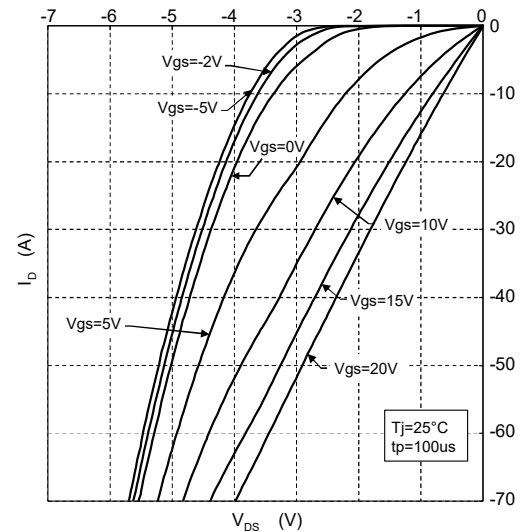


FIG. 7- $V_{GS(th)}$ vs T_J

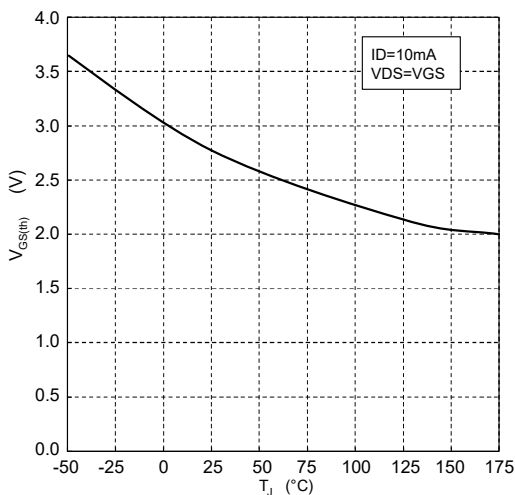
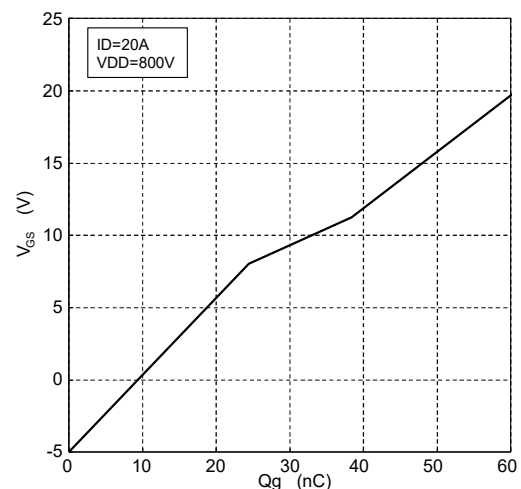


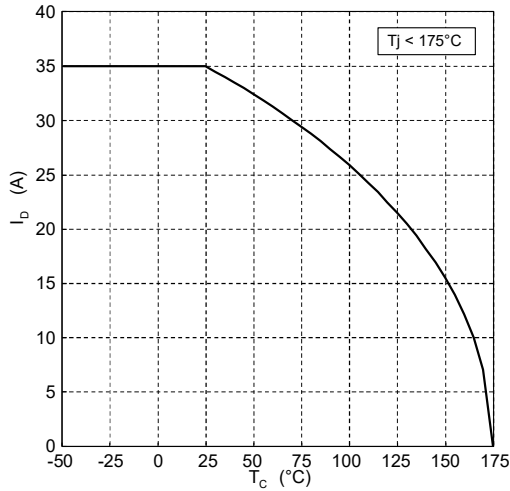
FIG. 8-Gate Charge Characteristics



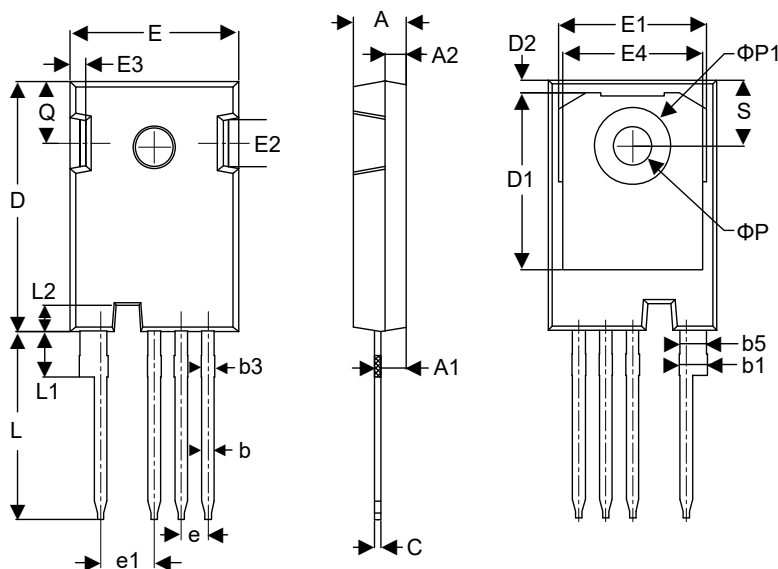


Typical Performance

FIG. 9- I_D vs T_C



Package Outline Dimensions



Symbol	Dimensions in millimeters		Dimensions in inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	0.190	0.206
A1	2.29	2.54	0.090	0.100
A2	1.91	2.16	0.075	0.086
b	1.07	1.33	0.042	0.053
b1	2.39	2.94	0.094	0.116
b3	1.07	1.60	0.042	0.063
b5	2.39	2.69	0.094	0.106
C	0.55	0.68	0.021	0.027
D	23.30	23.60	0.917	0.930
D1	16.25	17.65	0.639	0.695
D2	0.95	1.25	0.037	0.050
E	15.75	16.13	0.620	0.636
E1	13.10	14.15	0.515	0.558
E2	3.68	5.10	0.144	0.201
E3	1.00	1.90	0.039	0.075
E4	12.38	13.43	0.487	0.529
e	2.54 BSC		0.100 BSC	
e1	5.08 BSC		0.200 BSC	
L	17.31	17.82	0.681	0.702
L1	3.97	4.37	0.156	0.173
L2	2.35	2.65	0.092	0.105
ΦP	3.51	3.65	0.138	0.144
ΦP1	7.19 REF		0.284 REF	
Q	5.49	6.00	0.216	0.237
S	6.04	6.30	0.237	0.249

TO-247-4L

Dimensions in inches and (millimeters)



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